

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-21 (canceled)

Claim 22 (original): A film formation method in a film formation chamber, comprising the step of:

simultaneously operating first evaporation means and second evaporation means in the film formation chamber,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished, and

wherein the film formation chamber is connected with first exhaust means and second exhaust means.

Claim 23 (original): A film formation method in a film formation chamber, comprising the step of:

operating the first evaporation means and the second evaporation means in succession,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished, and

wherein the film formation chamber is connected with first exhaust means and second exhaust means.

Claim 24 (original): A film formation method in a film formation chamber, comprising the step of:

operating the first evaporation means and the second evaporation means in succession without time interruption,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished, and

wherein the film formation chamber is connected with first exhaust means and second exhaust means.

Claim 25 (original): A film formation method in a film formation chamber, comprising the step of:

simultaneously operating first evaporation means and second evaporation means in the film formation chamber,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished and an average surface roughness of the surface of the inner wall is 5 nm or less, and

wherein the film formation chamber is connected with a cryopump and a dry pump.

Claim 26 (original): A film formation method in a film formation chamber, comprising the step of:

operating the first evaporation means and the second evaporation means in succession,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished and an average surface roughness of the surface of the inner wall is 5 nm or less, and

wherein the film formation chamber is connected with a cryopump and a dry pump.

Claim 27 (original): A film formation method in a film formation chamber, comprising the step of:

operating the first evaporation means and the second evaporation means in succession without time interruption,

wherein the first evaporation means comprises a first plurality of evaporation sources and the second evaporation means comprises a second plurality of evaporation sources,

wherein a surface of an inner wall of the film formation chamber is electrolytic-polished and an average surface roughness of the surface of the inner wall is 5 nm or less, and wherein the film formation chamber is connected with a cryopump and a dry pump.

Claim 28 (original): A film formation method comprising the steps of:

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a first organic compound film in a first film formation chamber which includes a plurality of evaporation sources;

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a second organic compound film in a second film formation chamber which includes a plurality of evaporation sources; and

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a

third organic compound film in a third film formation chamber which includes a plurality of evaporation sources,

wherein the first organic compound film, the second organic compound film, and the third organic compound film exhibit light emission of different colors.

Claim 29 (original): A film formation method comprising the steps of:

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a first organic compound film in a first film formation chamber which includes a plurality of evaporation sources;

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a second organic compound film in a second film formation chamber which includes a plurality of evaporation sources; and

vapor-depositing a plural kinds of organic compounds simultaneously and successively changing a concentration of each of the plural kinds of organic compounds to thereby form a third organic compound film in a third film formation chamber which includes a plurality of evaporation sources,

wherein the first organic compound film, the second organic compound film, and the third organic compound film exhibit light emission of different colors, and

wherein a surface of an inner wall of each of the first film formation chamber, the second film formation chamber, and the third film formation chamber is electrolytic-polished.

Claim 30 (original): A film formation method according to claim 29, wherein an average surface roughness of the surface of the inner wall in the first film formation chamber, the second film formation chamber, and the third film formation chamber is 5 nm or less.

Claim 31 (original): A film formation method according claim 28, wherein, in the same formation chamber, a first functional region comprising a first organic compound is formed and a second functional region comprising a second organic compound is formed.

Claim 32 (original): A film formation method according claim 29, wherein, in the same formation chamber, a first functional region comprising a first organic compound is formed and a second functional region comprising a second organic compound is formed.

Claim 33 (original): A film formation method according to claim 31, wherein a mixed region comprising the first organic compound and the second organic compound is formed in an interface between the first functional region and the second functional region.

Claim 34 (original): A film formation method according to claim 32, wherein a mixed region comprising the first organic compound and the second organic compound is formed in an interface between the first functional region and the second functional region.

Claim 35 (original): A film formation method according to claim 31, wherein each of the first organic compound and the second organic compound is an organic compound comprising one of a hole injection property, a hole transport property, an emitting property, a blocking property, an electron transport property, and an electron injection property, and the first and second organic compounds are formed of different organic compounds.

Claim 36 (original): A film formation method according to claim 32, wherein each of the first organic compound and the second organic compound is an organic compound comprising one of a hole injection property, a hole transport property, an emitting property, a blocking property, an electron transport property, and an electron injection property, and the first and second organic compounds are formed of different organic compounds.

Claim 37 (original): A film formation method according to claim 31, wherein a second mixed region comprising the second organic compound and a third organic compound is formed in a part of the second functional region.

Claim 38 (original): A film formation method according to claim 32, wherein a second mixed region comprising the second organic compound and a third organic compound is formed in a part of the second functional region.

Claim 39 (original): A film formation method according to claim 37, wherein the third organic compound is an organic compound with a light emitting property; and the first, second, and third organic compounds are formed of different organic compounds.

Claim 40 (original): A film formation method according to claim 38, wherein the third organic compound is an organic compound with a light emitting property; and the first, second, and third organic compounds are formed of different organic compounds.

Claim 41 (original): A film formation method according to of claim 31, wherein the first functional region comprises an organic compound with a hole transport property, and the second functional region comprises an organic compound with an electron transport property.

Claim 42 (original): A film formation method according to of claim 32, wherein the first functional region comprises an organic compound with a hole transport property, and the second functional region comprises an organic compound with an electron transport property.

Claim 43 (original) A film formation method according to claim 35, wherein an aromatic diamine compound is used as the organic compound with the hole transport property.

Claim 44 (original): A film formation method according to claim 36, wherein an aromatic diamine compound is used as the organic compound with the hole transport property.

Claim 45 (original): A film formation method according to claim 35, wherein one of a metallic complex including quinoline skeleton, a metallic complex including benzoquinoline skeleton, an oxadiazole derivative, a triazole derivative, and a phenanthroline derivative is used as the organic compound with the electron transport property.

Claim 46 (original): A film formation method according to claim 36, wherein one of a metallic complex including quinoline skeleton, a metallic complex including benzoquinoline skeleton, an oxadiazole derivative, a triazole derivative, and a phenanthroline derivative is used as the organic compound with the electron transport property.

Claim 47 (original): A film formation method according to claim 35, wherein a metallic complex including quinoline skeleton, a metallic complex including benzoxazole skeleton, or a metallic complex including benzothiazole skeleton is used as the organic compound with the light emitting property.

Claim 48 (original): A film formation method according to claim 36, wherein a metallic complex including quinoline skeleton, a metallic complex including benzoxazole skeleton, or a metallic complex including benzothiazole skeleton is used as the organic compound with the light emitting property.